



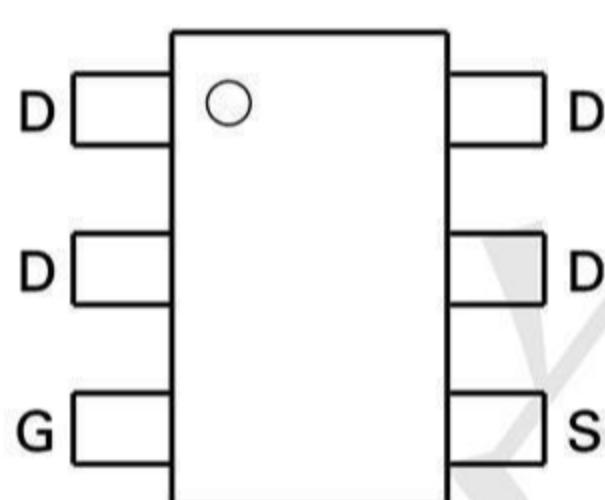
Product Summary

- 100V / 3A
- $R_{DS(ON)} = 87m\Omega$ (Typ) @ $V_{GS} = -10V$
- Reliable and Rugged
- Lead Free and Green Devices Available
(RoHS Compliant)

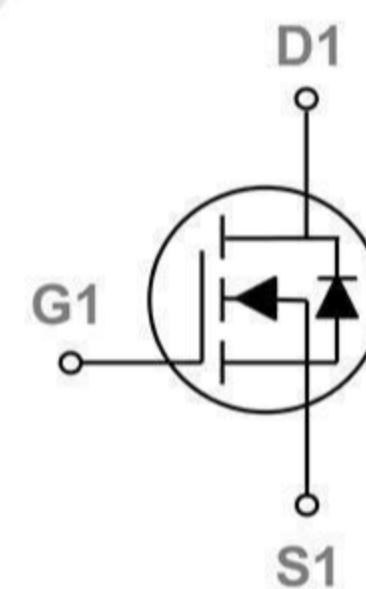
Application

- DC-DC Converters.
- Load Switch.
- Power Management.

Package and Pin Configuration



Circuit diagram



Marking: 362P Or BGTPM

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

| Parameter | Symbol | Value | Unit |
|--|-----------------|----------|--------------|
| Drain-Source Voltage | V_{DS} | 100 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Continuous Drain Current | I_D | 3 | A |
| Pulsed Drain Current (note 1) | I_{DM} | 20 | A |
| Power Dissipation | P_D | 1.7 | W |
| Thermal Resistance from Junction to Ambient (note 2) | $R_{\theta JA}$ | 106 | $^\circ C/W$ |
| Junction Temperature | T_J | 150 | $^\circ C$ |
| Storage Temperature | T_{STG} | -55~+150 | $^\circ C$ |



TECH PUBLIC

台舟电子

TPSI3476DV-T1-GE3

100V N-CHANNEL ENHANCEMENT MODE MOSFET

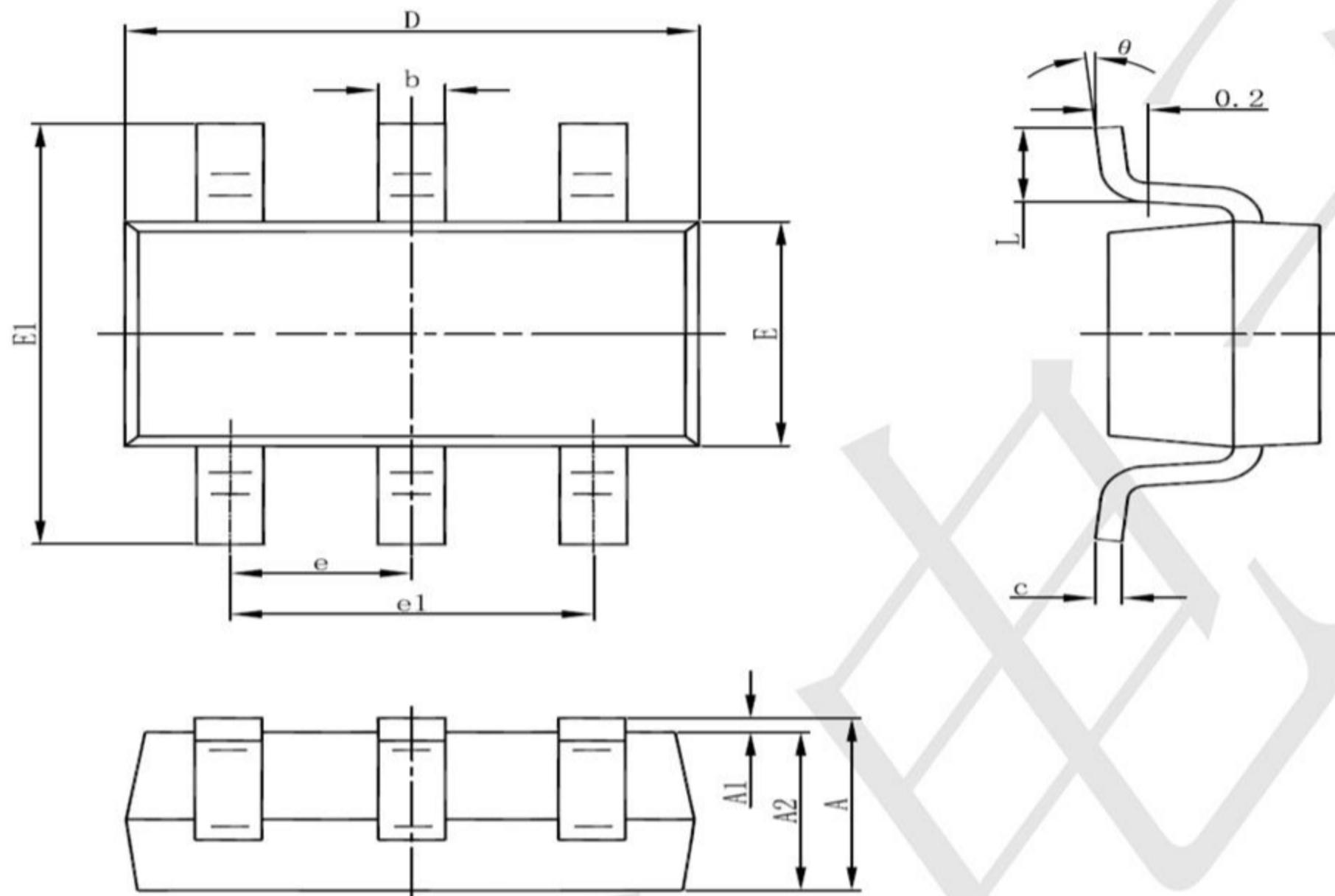
www.sot23.com.tw

Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

| Parameter | Symbol | Test conditions | Min | Typ | Max | Unit |
|--|-----------------------------|---|-----|------|-----------|------------------|
| Static Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | $V_{(\text{BR})\text{DSS}}$ | $V_{\text{GS}}=0\text{V}, I_D=250\mu\text{A}$ | 100 | | | V |
| Gate-Threshold Voltage ^(Note3) | $V_{\text{GS}(\text{th})}$ | $V_{\text{DS}}=V_{\text{GS}}, I_D=250\mu\text{A}$ | 1.2 | | 2.5 | V |
| Gate-Body Leakage Current | I_{GSS} | $V_{\text{GS}}=\pm 20\text{V}, V_{\text{DS}}=0\text{V}$ | | | ± 100 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{\text{DS}}=60\text{V}, V_{\text{GS}}=0\text{V}$ | | 1 | | μA |
| Drain-Source On-Resistance ^(Note3) | $R_{\text{DS}(\text{on})}$ | $V_{\text{GS}}=10\text{V}, I_D=3\text{A}$ | 87 | 125 | | $\text{m}\Omega$ |
| Forward Transconductance ^(Note3) | g_{fs} | $V_{\text{DS}}=5\text{V}, I_D=2.8\text{A}$ | 11 | | | S |
| Dynamic Characteristics^(Note4) | | | | | | |
| Input Capacitance | C_{iss} | $V_{\text{DS}}=50\text{V}, V_{\text{GS}}=0\text{V}, f=1\text{MHz}$ | 600 | | | |
| Output Capacitance | C_{oss} | | 60 | | | pF |
| Reverse Transfer Capacitance | C_{rss} | | 25 | | | |
| Switching Characteristics^(Note4) | | | | | | |
| Total Gate Charge | Q_g | $V_{\text{DS}}=48\text{V}, V_{\text{GS}}=10\text{V}, I_D=2.6\text{A}$ | | 12 | | |
| Gate-Source Charge | Q_{gs} | | | 4.1 | | nC |
| Gate-Drain Charge | Q_{gd} | | | 4.5 | | |
| Turn-on Delay Time | $t_{\text{d}(\text{on})}$ | | | 5.0 | | |
| Turn-on Rise Time | t_r | | | 2.6 | | |
| Turn-off Delay Time | $t_{\text{d}(\text{off})}$ | | | 16.1 | | ns |
| Turn-off Fall Time | t_f | | | 2.3 | | |
| Drain-Source Diode Characteristics | | | | | | |
| Diode Forward Voltage ^(Note3) | V_{SD} | $V_{\text{GS}}=0\text{V}, I_s=1.5\text{A}$ | | | 1.2 | V |
| Diode Forward Current ^(Note2) | I_s | | | | 1.5 | A |
| Reverse Recovery Time | t_{rr} | $I_F=2.6\text{A}, \text{di}/\text{dt}=100\text{A}/\mu\text{s}$ ^(Note4) | | 35 | | nS |
| Reverse Recovery Charge | Q_{rr} | | | 53 | | μC |
| Forward Turn-On Time | t_{on} | Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD) | | | | |



SOT23-6 Package Information



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| | Min | Max | Min | Max |
| A | 1.050 | 1.250 | 0.041 | 0.049 |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 |
| A2 | 1.050 | 1.150 | 0.041 | 0.045 |
| b | 0.300 | 0.500 | 0.012 | 0.020 |
| c | 0.100 | 0.200 | 0.004 | 0.008 |
| D | 2.820 | 3.020 | 0.111 | 0.119 |
| E | 1.500 | 1.700 | 0.059 | 0.067 |
| E1 | 2.650 | 2.950 | 0.104 | 0.116 |
| e | 0.950(BSC) | | 0.037(BSC) | |
| e1 | 1.800 | 2.000 | 0.071 | 0.079 |
| L | 0.300 | 0.600 | 0.012 | 0.024 |
| θ | 0° | 8° | 0° | 8° |